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rf MEMS Devices Compatible with SiGe and rf CMOS Processing

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November 14, 2005

Outline

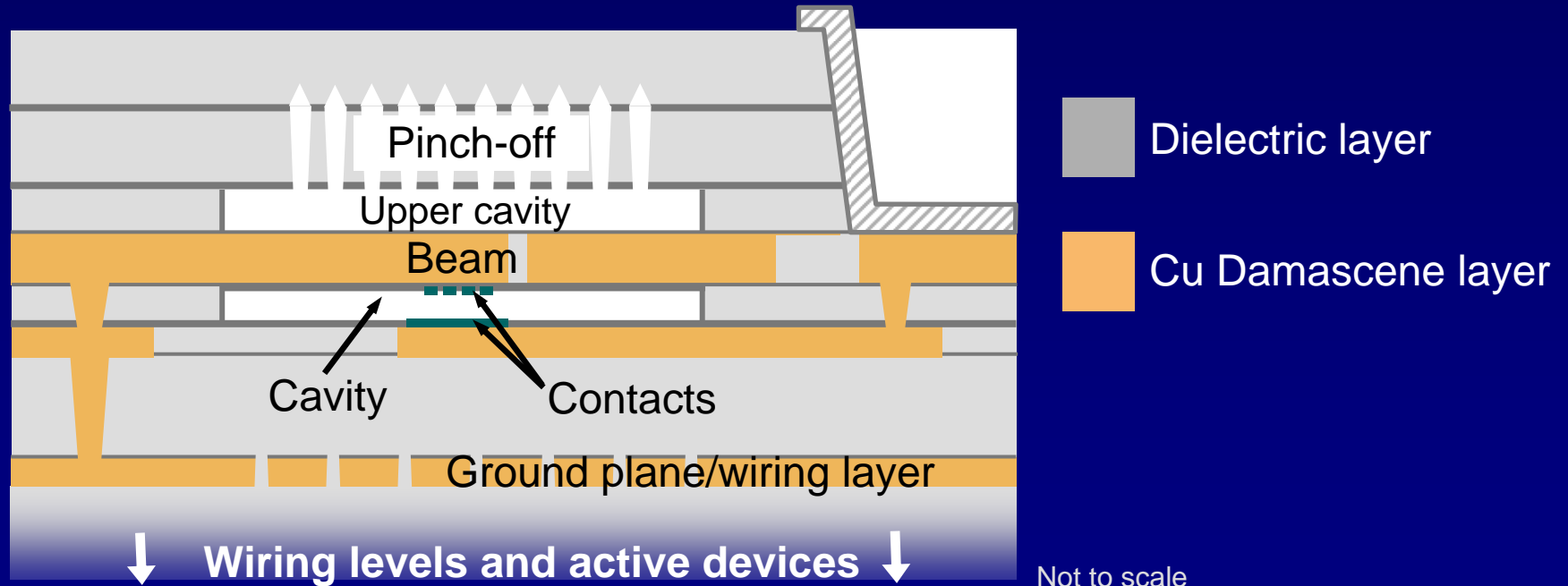
- IBM approach to rf MEMS
- Switches
- Resonators and filters



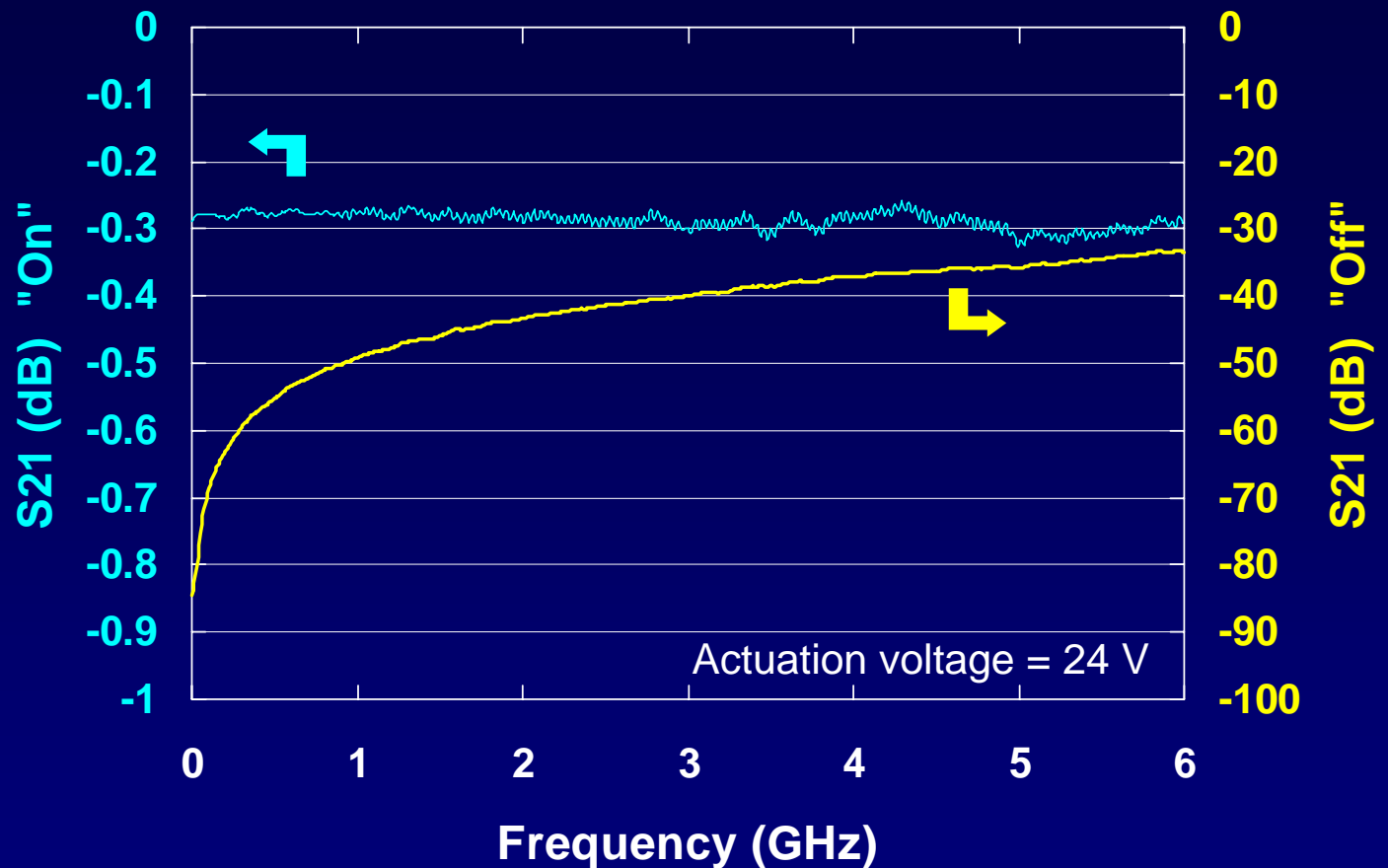
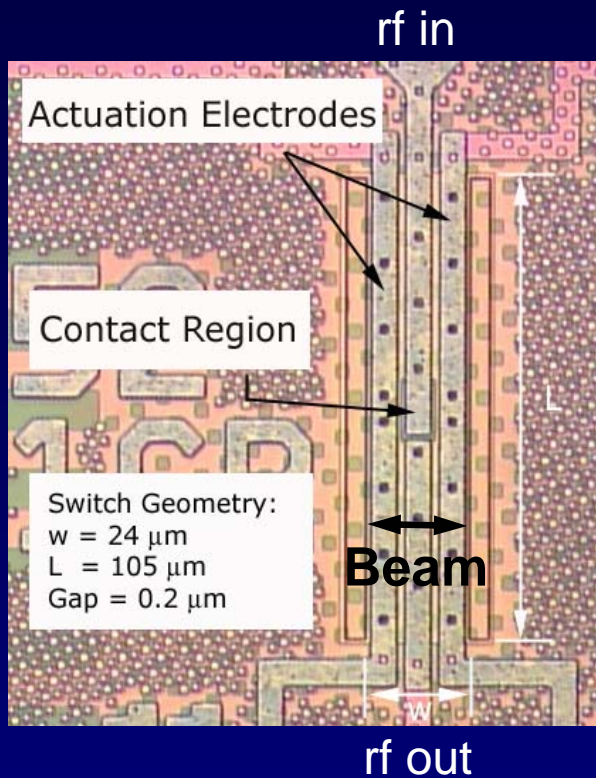
Thomas J. Watson Research Center

IBM's Approach to Integrated rf MEMS

- MEMS switches, resonators, and filters which can be integrated within the wiring levels for SiGe or analog CMOS IC's
 - Better performance, smaller size than discrete MEMS components
 - Potential for lower assembled cost as technology matures
 - Could enable novel radio architectures requiring many MEMS devices
- Devices built in a CMOS manufacturing environment with no new tools
- Process flow that allows fabrication of multiple types of devices
- Fully encapsulated devices at wafer level

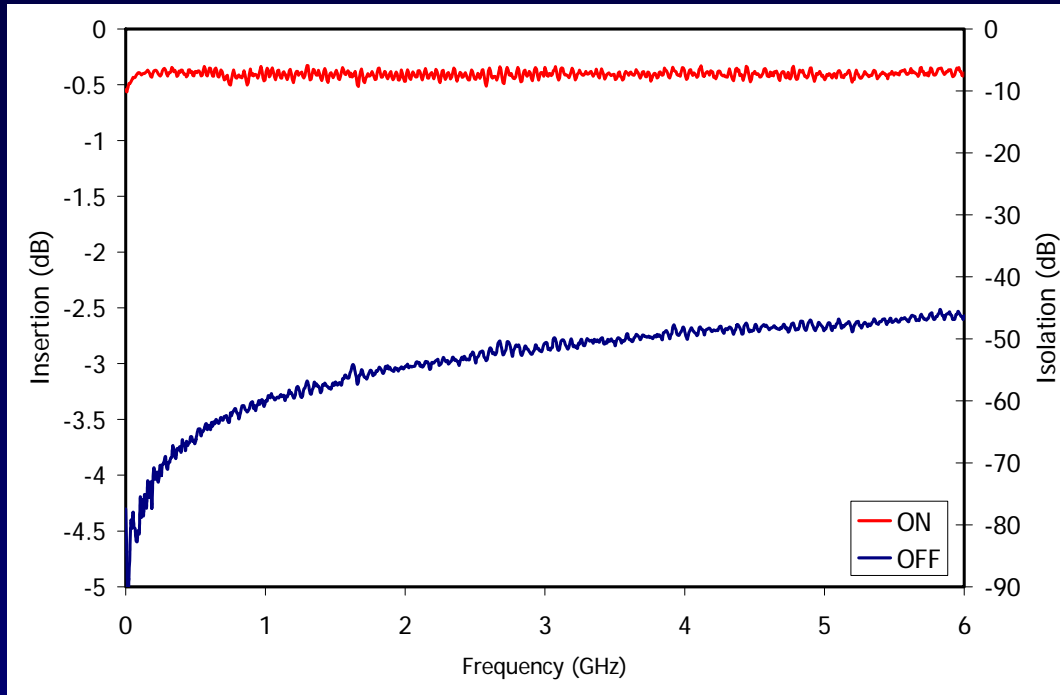


MEMS Switch Insertion Loss and Isolation

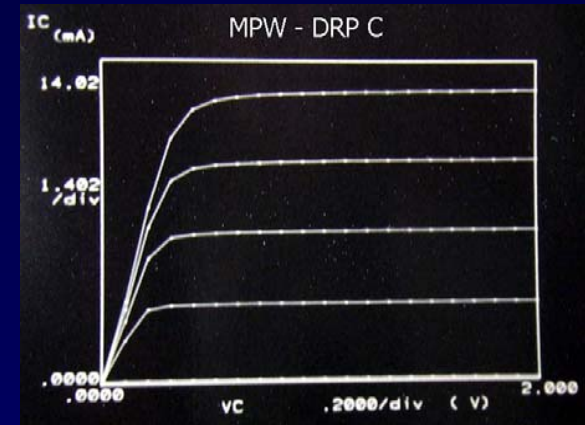


- Insertion loss 0.3 dB
- Isolation >32 dB up to 6 GHz

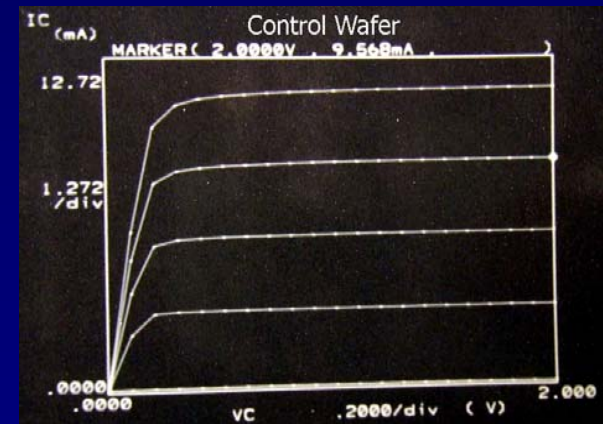
Switches Integrated on Functional SiGe IC's



- Working with a partner, switches were demonstrated on functional SiGe wafers
- No degradation of transistor characteristics due to MEMS processing
- Initiating work with other partners for a more extensive demonstration



Transistor on wafer with MEMS devices



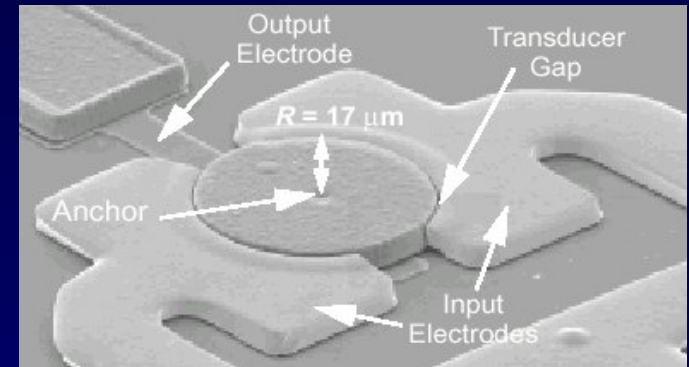
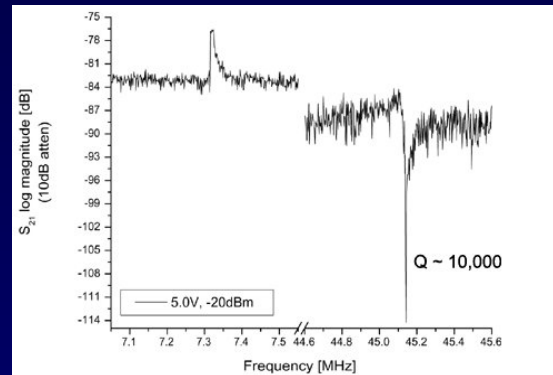
Transistor on wafer with no MEMS devices

MEMS Resonators and Filters

- Electrostatically actuated mechanical resonators and filters do not scale well to GHz frequencies and have very high impedance

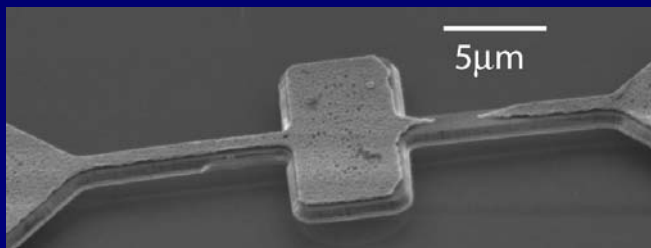


IBM - Cantilever beam

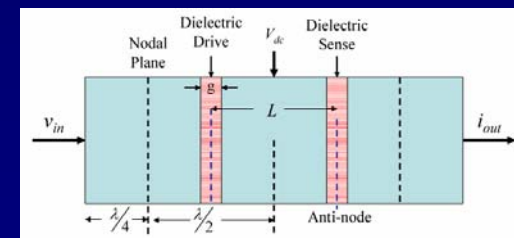


Nguyen - Disk resonator

- Evaluated attractive new technologies and have started fabricating new devices suitable for integration



Draper Labs – Piezoelectric bar resonator



Bhave et al. – Internal electrostatic transduction

- IBM strengths: Superior process and integration technology
Ultra-high resolution lithography for tight frequency control
Path to manufacturing

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